

【July 11th, Wednesday】

Opening Session (13:00-13:10)

Plenary Session (13:10-14:00)

Chair : A. Wakahara (Toyohashi University of Technology)

Plenary 13:10 (50min) ... 1
Molecular beam epitaxy and creation of new semiconductors and new devices
H. Asahi
Osaka University

Session We1: III-Nitride Growth I (14:00-15:00)

Chair : M. Sugiyama (The University of Tokyo)

We1-1 [Invited] 14:00 (30min) ... 5
Hydrogen evolution by water reduction using nitride photoelectrodes
K. Ohkawa
Tokyo University of Science

We1-2 14:30 (3min+poster) ... 7
Effects of AlGaIn thin layer on n-type GaN for photoelectrochemical reactions
A. Nakamura, M. Sugiyama, and K. Fujii
The University of Tokyo

We1-3 14:33 (3min+poster) ... 11
Impact of (GaN/AlN) alternating-source-feeding layer for the GaN growth on (111)Si substrates by RF-MBE
D. Tajimi, T. Igaki, Y. Sugiura, T. Yamaguchi, and T. Honda
Kogakuin University

We1-4 14:36 (3min+poster) ... 13
Structural characterization of coherently-grown and relaxed AlN/GaN short-period superlattices on 6H-SiC (0001) substrates by plasma-assisted molecular-beam epitaxy
M. Kaneko, R. Kikuchi, H. Okumura, T. Kimoto, and J. Suda
Kyoto University

We1-5 14:39 (3min+poster) ... 15
Metalorganic chemical vapor deposition growth and optical characteristics of site-controlled single GaN/AlGaIn quantum dots in nanowires
K. Choi, M. Arita, and Y. Arakawa
The University of Tokyo

We1-6 14:42 (3min+poster) ... 17
AlN/air distributed Bragg reflector using GaN sublimation from micro-cracks of AlN
T. Mitsunari, T. Tanikawa, Y. Honda, M. Yamaguchi, and H. Amano
Nagoya University

We1-7 14:45 (3min+poster) ... 19
Optical analysis of indium incorporation of micro-facets grown on nonpolar GaN bulk substrate
B. Ma, D. Jinno, H. Miyake, and K. Hiramatsu
Mie University

We1-8 14:48 (3min+poster) ... 21
Selective area growth of semipolar GaN layers on patterned sapphire substrate with wide terrace by MOVPE and HVPE
A. Ishikawa, M. Ueno, K. Yamane, N. Okada, K. Tadatomo
Yamaguchi University

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Research of double polarities selective area growth of GaN by using MOVPE Y. Fujita*, Y. Inoue*, Y. Takano*, M. Sumiya**, S. Fuke*, and T. Nakano* *Shizuoka University, **National Institute for Materials Science			
We1-10	14:54 (3min+poster)	...	25
Growth temperature tuning for GaN lateral growth on c-plane GaN template by RF-MBE H. Kato, T. Iwatsuki, Y. Shirai, Y. Hirota, T. Maruyama and S. Naritsuka Meijo University			
We1-11	14:57 (3min+poster)	...	27
Growth of high quality LT GaN layer with indium surfactant I. S. Shin*, K. Wang**, T. Araki**, E. Yoon*, and Y. Nanishi*** *Seoul National University, **Ritsumeikan University			

Break (15:00-15:15)

Session We2: New Materials (15:15-16:57)

Chair : Y. Kangawa (Kyushu Univeristy)

We2-1 [Invited] 15:15 (30min)		...	29
Electronic states of epitaxial graphene F. Komori The University of Tokyo			
We2-2	15:45 (3min+poster)	...	31
Graphene nanoribbons grown by molecular beam epitaxy T. Kajiwara*, Y. Nakamori*, M. Takaki*, Y. Hagihara*, S. Tanaka*, K. Nakatsuji**, T. Yoshimura**, S. Yoshizawa**, and F. Komori** *Kyushu university, **The University of Tokyo			
We2-3	15:48 (3min+poster)	...	33
MMSi addition on diamond nucleation onto Si substrate T. Shige-eda, T. Tamura, and H. Isshiki The University of Electro-Communications			
We2-4	15:51 (3min+poster)	...	35
The development equipment of diamond powder using MPCVD S. Takigawa, K. Matsushima, T. Tamura, and H. Isshiki The University of Electro-Communications			
We2-5	15:54 (3min+poster)	...	37
Growth of AlC on sapphire, Silicon and SiC substrates Y. Ohnishi, D. Kim, and S. Sakai The University of Tokushima			
We2-6	15:57 (3min+poster)	...	39
Growth condition dependence of Ge doping into β -FeSi ₂ epitaxial film by MBE method K. Noda, Y. Terai, and Y. Fujiwara Osaka University			

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A new alloy system based on corundum structured oxides		
K. Kaneko, H. Ito, K. Akaiwa, N. Suzuki, and S. Fujita		
Kyoto University		
We2-8	16:03 (3min+poster)	... 43
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J. Kudou*, M. Takahara*, R. Aida*, K. Ishibashi*, I. Tsunoda*, K. Takakura*,		
H. Ohyama*, S. Funasaki**, T. Nakashima***, M. Shibuya****, and K. Murakami*****		
*Kumamoto National College of Technology, **Kyushu University, ***Chuo Denshi Kogyo Co. Ltd., ****Echo Mother,		
*****Japan Gas Chemi		
We2-9	16:06 (3min+poster)	... 45
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N. Suzuki, K. Kaneko, and S. Fujita		
Kyoto University		
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TiO ₂ particle production with flame synthesis method for nanoparticles by using flashing spray -influence of injection frequency and ambient temperature change to particle distribution -		
M. Oshima*, H. Miyamoto*, J. Senda**, and K. Ishida***		
*Fukui University of Tech., **Doshisha University, ***HORIBA, Ltd.		
We2-11	16:12 (3min+poster)	... 49
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Y. Nose, T. Nakamura, T. Yoshimura, A. Ashida, T. Uehara, and N. Fujimura		
Osaka Prefecture University		
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Characterization of ZnO crystal growth in $\pm c$ directions		
T. Nayuki and T. Yamauchi		
AsahiKasei		
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Ozone treatment of oxide surface for the fabrication of MgZnO films by molecular precursor method		
T. Yasuno, T. Oda, H. Nagai, H. Hara, Y. Sugiura, M. Sato, and T. Honda		
Kogakuin University		
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MOVPE growth of ZnO using Zn-TD as Zn source		
M. Kato, Y. Hotta, Y. Nabetani, T. Muranaka, T. Kato, and T. Matsumoto		
University of Yamanashi		
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K. Uno, Y. Tauchi, and I. Tanaka		
Wakayama University		
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Y. Shirai, Y. Hirota, T. Iwatsuki, H. Kato, and S. Naritsuka		
Meijo University		

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Photoluminescence and photoreflectance spectra of C60 and Si co-doped GaAs layers			
W. Ding [*] , A. Suzuki [*] , A. Fukuyama [*] , J. Nishinaga ^{**} , Y. Horikoshi ^{**} , and T. Ikari [*]			
[*] Miyazaki University, ^{**} Waseda University			
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Delocalization of electronic states formed by nitrogen pairs in GaAs			
M. Yamamoto, K. Kimura, Y. Harada, and T. Kita			
Kobe University			
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Growth and characterization of δ -doped nitrogen/GaAs superlattice			
K. Sumiya, M. Morifuji, Y. Oshima, and F. Ishikawa			
Osaka University			
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Molecular beam epitaxial growth of GaAsN nanowire			
F. Ishikawa and Y. Araki			
Osaka University			
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Electrical conduction property at InAs/Si(111) interface by selective-area MOVPE			
S. Watanabe, K. Watanabe, A. Higo, M. Sugiyama, and Y. Nakano			
The University of Tokyo			
We2-22	16:45 (3min+poster)	...	73
Growth characterization of dilute BGaP alloys grown by Molecular Beam Epitaxy			
N. Urakami [*] , F. Fukami [*] , H. Sekiguchi [*] , H. Okada ^{**} , and A. Wakahara [*]			
[*] Toyohashi University of Technology, ^{**} Electronics-Inspired Interdisciplinary Research Institute			
We2-23	16:48 (3min+poster)	...	75
The research on the possibility of the novel neutron detector using B GaN			
K. Atsumi, H. Kaneko, T. Nishioka, Y. Inoue, H. Mimura, T. Aoki, and T. Nakano			
Shizuoka University			
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Improvement of electrical properties of S doped n-type GaPN by alternately N supplied method			
Y. Nagamoto, K. Matsuoka, H. Sekiguchi, H. Okada, and A. Wakahara			
Toyohashi University of Technology			
We2-25	16:54 (3min+poster)	...	79
Growth of cubic AlN films on MgO substrate via 2-step cubic GaN buffer layer by RF-MBE			
M. Kakuda [*] , S. Morikawa [*] , S. Kuboya [*] , R. Katayama ^{**} , and K. Onabe [*]			
[*] The University of Tokyo, ^{**} Tohoku University			

Break (16:57-17:00)

Poster Session I (We1, We2) (17:00-19:00)

Dinner (19:00-20:00)

Rump Session (20:00-21:30)

“Materials and Devices for Solving Energy Issues”

~Young based chat session~

Organizers : A. Wakahara (*Toyohashi University of Technology*)
Y. Nabetani (*University of Yamanashi*)
T. Yamaguchi (*Kogakuin University*)
N. Okada (*Yamaguchi University*)
T. Oshima (*Tokyo Institute of Technology*)

Panelists : M. Sugiyama (*The University of Tokyo*)
A. Yamada (*Tokyo Institute of Technology*)

【July 12th, Thursday】

Session Th1: Doping and Properties of Novel Materials (8:30-10:18)

Chair : T. Suemasu (*Tsukuba University*)

Th1-1 [Invited] 8:30 (30min)	...	81
Electrically driven single photon source at room temperature in diamond		
N. Mizuochi		
Osaka University		
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Optical properties of boron doped diamond		
Y. Ota and T. Inushima		
Tokai University		
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Control of nuclear spin coherence in n-GaAs/AlGaAs (110) quantum well by nuclear electric resonance		
C. Zhang, J. Ishihara, M. Ono, Y. Ohno, and H. Ohno		
Tohoku University		
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Magneto-transport properties of YbFe ₂ O ₄ epitaxial thin films		
Y. Masuda, H. Yukawa, T. Yoshimura, A. Ashida, and N. Fujimura		
Osaka Prefecture University		
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Magneto transport properties of Si:Ce magnetic semiconductor thin films		
Y. Miyata, Y. Okuyama, T. Yoshimura, A. Ashida, and N. Fujimura		
Osaka Prefecture University		
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Photoluminescence properties of InGaAsN films on Ge(001) vicinal substrates		
K. Uesugi*, S. Kuboya*, S. Sanorpim**, and K. Onabe*		
*The University of Tokyo, **Chulalongkorn University		
Th1-7 9:15 (3min+poster)	...	93
Polarization properties in InGaN/GaN multiple quantum well on semipolar (1-101) GaN/Si		
M. Kushimoto, T. Tanikawa, Y. Honda, M. Yamaguchi, and H. Amano		
Nagoya University		
Th1-8 9:18 (3min+poster)	...	95
Emission properties of localized excitons in weakly excited Al-rich AlGa _x N/AlN quantum wells		
T. Oto, R. G. Banal, M. Funato, and Y. Kawakami		
Kyoto University		
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Structural and optical characterization of homoepitaxial AlN film		
R. Ishii, K. Matsuda, R. G. Banal, M. Funato, and Y. Kawakami		
Kyoto University		
Th1-10 9:24 (3min+poster)	...	99
Hydrostatic and uniaxial deformation potentials in aluminum nitride: Breakdown of the quasicubic approximation in AlN		
R. Ishii, A. Kaneta, M. Funato, and Y. Kawakami		
Kyoto University		

Th1-11	9:27 (3min+poster)	...	101
Variation in SOI Seebeck coefficient by an external bias			
F. Salleh ^{***} , K. Miwa [*] , and H. Ikeda [*]			
[*] Shizuoka University,			
^{**} Research Fellow of the Japan Society for the Promotion of Science			
Th1-12	9:30 (3min+poster)	...	103
Thermoelectric power measurement of self-catalyzed Si-doped GaAs nanowires grown by MBE-VLS			
M. Yamaguchi, J. H. Paek, and H. Amano			
Nagoya University			
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Effect of Be doping on the photoreflectance and photoluminescence spectra of catalyst free MBE-VLS grown GaAs nanowires on Si (111) substrate			
A. Suzuki [*] , A. Fukuyama [*] , J. H. Paek ^{**} , M. Yamaguchi ^{**} , and T. Ikari [*]			
[*] University of Miyazaki, ^{**} Nagoya University			
Th1-14	9:36 (3min+poster)	...	107
Electrical characteristics of C ₆₀ , Si codoped GaAs layers grown by MEE			
J. Nishinaga and Y. Horikoshi			
Waseda University			
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Persistent photoconductivity in p-Type 4H-SiC bulk crystals			
T. Okuda, H. Miyake, T. Kimoto, and J. Suda			
Kyoto University			
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Impurity incorporation of Si-doped GaN by alternate supply using MOVPE			
K. Yamashita, Y. Honda, M. Yamaguchi, and H. Amano			
Nagoya University			
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Eu luminescence properties in Eu,Mg,Si-codoped GaN			
D. Lee, R. Wakamatsu, T. Matsuno, R. Hasegawa, A. Koizumi, Y. Terai,			
and Y. Fujiwara			
Osaka University			
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Growth and optical properties of Eu-doped GaN grown with flow-rate modulation epitaxy			
T. Matsuno, D. Lee, R. Wakamatsu, A. Koizumi, Y. Terai, and Y. Fujiwara			
Osaka University			
Th1-19	9:51 (3min+poster)	...	117
Anomalous luminescence peak observed in Eu-doped gallium nitride			
R. Wakamatsu, A. Koizumi, D. Lee, Y. Terai, and Y. Fujiwara			
Osaka University			
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Luminescence properties of Eu-doped GaN grown by selective-area organometallic vapor phase epitaxy			
R. Hasegawa [*] , R. Wakamatsu [*] , A. Koizumi [*] , H. Ofuchi ^{**} , D. Lee [*] , Y. Terai [*] ,			
T. Honma ^{**} , and Y. Fujiwara [*]			
[*] Osaka University, ^{**} JapanSynchrotron Radiation Research Institute			

Th1-21	9:57 (3min+poster)	...	123
Photoluminescence properties of Yb-doped ZnO grown by sputtering-assisted MOCVD W. Miao, Y. Terai, T. Tsuji, W. Cao, and Y. Fujiwara Osaka University			
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PL properties of Eu ³⁺ in Eu,Au-codoped ZnO grown by SA-MOCVD T. Tsuji, Y. Terai, W. Miao, H. Hatagishi and Y. Fujiwara Osaka University			
Th1-23	10:03 (3min+poster)	...	127
Metallic composition dependence on Erbium Yttrium Silicate films fabricated by radical assisted sputtering T. Shinagawa*, T. Nakajima*, T. Sugawara**, Y. Jiang**, T. Kimura*, and H. Isshiki* *The University of Electro-Communications, **Shincron Co., Ltd.			
Th1-24	10:06 (3min+poster)	...	129
Cooperative upconversion in Er _{0.45} Y _{1.55} SiO ₅ crystalline waveguide T. Nakajima*, T. Shinagawa*, T. Sugawara**, Y. Jiang**, T. Kimura*, and H. Isshiki* *The University of Electro-Communications, **Shincron Co., Ltd.			
Th1-25	10:09 (3min+poster)	...	131
Electro-optic effect of Er _x Y _{2-x} SiO ₅ crystals measured by electric field modulation reflectance spectroscopy Y. Terada, T. Kimura, and H. Isshiki The University of Electro-Communications			
Th1-26	10:12 (3min+poster)	...	133
Fabrication of conductive tin-doped α-Ga ₂ O ₃ grown by mist CVD method K. Akaiwa and S. Fujita Kyoto University			
Th1-27	10:15 (3min+poster)	...	135
Effect of iron doping for indium tin oxide nanoparticle thin films A. Fujimoto*, T. Higaki*, Y. Kimura*, Y. Matsuura*, T. Kamimura*, M. Nakamoto**, Y. Kashiwagi**, M. Yamamoto**, M. Saitoh**, T. Ohno**, and S. Furuta*** *Osaka Institute of Technology, **Osaka Municipal Technical Research Institute, ***Tomoe Works Co., Ltd.			

Break (10:18-10:20)

Poster Session II (Th1) (10:20-12:00)

Lunch (12:00-13:00)

Session Th2: Electron Devices (13:00-14:06)

Chair : K. Shiojima (*University of Fukui*)

Th2-1 [Invited] 13:00 (30min)	...	137
Single-crystal gallium oxide (Ga₂O₃) metal-semiconductor field-effect transistors M. Higashiwaki National Institute of Information and Communications Technology		

Th2-2	13:30 (3min+poster)	...	139
Epitaxial stabilization of γ -phase Ga_2O_3 thin films by Mist CVD			
T. Oshima*, T. Nakazono*, A. Mukai*, and A. Ohtomo***			
*Tokyo Tech, **ALCA			
Th2-3	13:33 (3min+poster)	...	141
Device-quality β - Ga_2O_3 epitaxial films fabricated by ozone MBE			
K. Sasaki**, A. Kuramata*, T. Masui***, E. G. Villora****, K. Shimamura****, and S. Yamakoshi*			
*Tamura Corporation, **National Institute of Information and Communications Technology, ***Koha Co., Ltd., ****National Institute for Materials Science			
Th2-4	13:36 (3min+poster)	...	143
Vertical breakdown characteristics of AlGaIn/GaN HFET with carbon-doped GaN on conductive GaN substrate			
T. Sugiyama, Y. Honda, M. Yamaguchi, and H. Amano			
Nagoya University			
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p-Channel AlN/Diamond heterojunction field effect transistors			
M. Imura*, R. Hayakawa*, H. Ohsato*, E. Watanabe*, D. Tsuya*, M. Liao*,			
Y. Koide*, H. Amano**, T. Matsumoto****, and S. Yamasaki****			
*National Institute for Materials Science, **Nagoya University, ***AIST, ****University of Tsukuba			
Th2-6	13:42 (3min+poster)	...	147
Channel polarity of organic field-effect transistors using TMTSF-TCNQ crystals grown by solution process			
T. Nawata, H. Yamakado, K. Uno, and I. Tanaka			
Wakayama University			
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Electrical properties of oxide TFT with an IGZO/ AlO_x stack grown by non-vacuum mist chemical vapour deposition			
T. Kawaharamura, D. Wang, and M. Furuta			
Kochi University of Technology			
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Electron irradiation degradation of gate length modulated strained-Si pMOSFETs			
R. Watanabe*, Y. Nagaoka*, T. Nakashima**, M. Yoneoka*, I. Tsunoda*,			
K. Takakura*, M.B. Gonzalez****, E. Simoen***, and C. Claeys****			
*Kumamoto National College of Technology, **Chuo Denshi Kogyo Co. Ltd., ***imec, ****E.E. Dept., KU Leuven			
Th2-9	13:51 (3min+poster)	...	155
Stress evaluation by Raman Spectroscopy in 2MeV electron irradiated SiGe/Si diodes			
T.Nakashima****, I. Tsunoda**, K. Takakura**, M. Yoneoka**, H. Ohyama**,			
N. Naka***, K. Yoshino****, E. Simoen****, and C. Claeys****			
*Chuo Denshi Kogyo Co. Ltd, **Kumamoto National College of Technology, ***HORIBA Ltd, ****University of Miyazaki, *****imec, *****E.E Dept., KU Leuven			
Th2-10	13:54 (3min+poster)	...	157
2 MeV Electron irradiation damage of commercial JFET			
S. Sakiyama, D. Tsumagarim, M. Moriuchi, K. Takakura, I. Tsunoda,			
M. Yoneoka, H. Ohyama, and T. Nakashima			
Kumamoto National College of Technology			
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Electron-irradiation damage of commercial Monolithic Ceramic Capacitors			
M. Moriuchi, K. Takakura, I. Tsunoda, and H. Ohyama			
Kumamoto National College of Technology			

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Y. Ushiyama, N. Marumo, T. Muranaka, Y. Nabetani, and T. Matsumoto
University of Yamanashi

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Pt thickness and annealing temperature dependence of magnetic anisotropy of Co/Pt based electrodes for perpendicular magnetic tunnel junctions
S. Ishikawa, H. Sato, M. Yamanouchi, S. Ikeda, S. Fukami, F. Matsukura,
and H. Ohno
Tohoku University,

Session Th3: Surface and Interface (14:06-14:36)

Chair : T. Araki (Ritsumeikan University)

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STM observation of novel nano-string structures on Cr-deposited Au(111)
S. Kaku and J. Yoshino
Tokyo Institute of Technology

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Comparative study of initial growth of MnAs on GaAs(001) c(4×4)α and (6×6) reconstructions
M. Hiraoka, S. Kaku, and J. Yoshino
Tokyo Institute of Technology

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Polarity determination of AlN by convergent beam electron diffraction method based on transmission electron microscopy
M. Imura*, K. Nakajima*, Y. Koide*, H. Amano**, and K. Tsuda***
*National Institute for Materials Science, **Nagoya University, ***Tohoku University

Th3-4 14:15 (3min+poster) ...171
Angled-resolved XPS measurements of In-polar and N-polar InN films
R. Amiya, T. Yamaguchi, D. Tajimi, M. Hayashi, Y. Sugiura, T. Honda, T. Araki**, and Y. Nanishi***
*Kogakuin University, **Ritsumeikan University, ***Seoul National University

Th3-5 14:18 (3min+poster) ...173
Surface and Bulk Electronic Structure of Mg-doped InN Analyzed by Hard X-ray Photoelectron Spectroscopy
M. Imura*, S. Tsuda*, T. Nagata*, Y. Koide*, A. L. Yang**, Y. Yamashita*,
H. Yoshikawa*, K. Kobayashi*, M. Kaneko**, T. Yamaguchi**, N. Uematsu**,
T. Araki**, and Y. Nanishi**
*National Institute for Materials Science, **Ritsumeikan University

Th3-6 14:21 (3min+poster) ...175
X-ray photoelectron spectroscopy spectra of Ga- and N-face (0001)GaN around the valence-band binding energy
Y. Sugiura, D. Tajimi, R. Amiya, T. Yamaguchi, and T. Honda
Kogakuin University

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Band alignment of carbon nanotube/n-type 6H-SiC heterojunction determined by photoelectron spectroscopy
T. Maruyama*, S. Sakakibara*, S. Naritsuka*, H. Yamane**, and N. Kosugi**
*Meijo University, **IMS

Th3-8 14:27 (3min+poster) ...179
Interface states in GaAs/p-GaAs_{1-x}Bi_x heterointerface investigated by admittance spectroscopy
T. Fuyuki, S. Kashiyama, K. Oe, and M. Yoshimoto
Kyoto Institute of Technology

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Electrical properties of 2D hole gas in GaN/AlGaN heterostructure
A. Nakajima, M. Ogura, S. Nishizawa, and H. Ohashi
AIST

Th3-10 14:33 (3min+poster) ...183
Investigation of the relationship between 2DEG density and reverse leakage current in AlGaIn/GaN Schottky barrier diodes
T. Tsuchiya, A. Terano, and K. Mochizuki
Hitachi Ltd.

Break (14:36-15:00)

Session Th4: III-Nitride Growth II (15:00-15:39)

Chair : T. Yamaguchi (*Kogakuin University*)

Th4-1 15:00 (3min+poster) ...185
Spontaneous separation using thermal stress of GaN thick film grown by Hydride Vapor Phase Epitaxy
M. Ueno, K. Yamane, H. Furuya, N. Okada, and K. Tadatomo
Yamaguchi University

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Effects of stirring solution on the morphology of GaN grown by Na-flux method
Y. Harada, H. Iga, K. Murakami, H. Imabayashi, H. Takazawa, Y. Todoroki,
D. Matsuo M. Maruyama, M. Imade, M. Yoshimura, and Y. Mori
Osaka University

Th4-3 15:06 (3min+poster) ...189
Structural and optical properties of prismatic bulk GaN crystals grown by Ba-added Na flux method
H. Imabayashi, K. Murakami, D. Matsuo, H. Takazawa, Y. Todoroki,
A. Kitamoto, M. Maruyama, M. Imade, M. Yoshimura, and Y. Mori
Osaka University

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The effect of surface state of the seed substrate on the quality of GaN crystals grown by the Na flux method
M. Honjo, T. Fujimori, H. Takazawa, Y. Todoroki, H. Imabayashi, D. Matsuo,
K. Murakami, M. Maruyama, M. Imade, M. Yoshimura, and Y. Mori
Osaka University

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*Institute for Materials Research, Tohoku University, **CREST, Japan Science and Technology Agency			
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Poster Session IV (Fr1) (10:00-11:45)
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Special Session (13:00-15:20)

“New Development of Nano-Wire Semiconductor –The Light for Device Applications–”

Chair : A. Wakahara (Toyohashi University of Technology)

13:00 (5min)

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Toyohashi University of Technology

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National Institute for Materials Science

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Osaka University

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